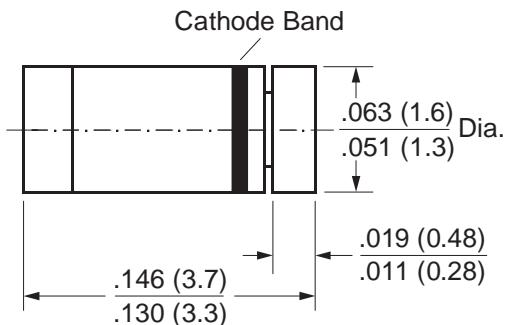




## Schottky Diodes

### MiniMELF (SOD-80C)



Dimensions in inches and (millimeters)

### Features

- For general purpose applications
- The LL103A, B, C series is a metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.
- The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications. Other applications are click suppression, efficient full wave bridges in telephone subsets, and blocking diodes in rechargeable low voltage battery systems.
- This diode is also available in the DO-35 case with type designation SD103A, B, C and in the SOD-123 case with type designation SD103AW, SD103BW, SD103CW.

### Mechanical Data

**Case:** MiniMELF Glass Case (SOD-80C)

**Weight:** approx. 0.05g

### Maximum Ratings & Thermal Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

| Parameter  | Symbol           | Value              | Unit |
|--|------------------|--------------------|------|
| Peak Inverse Voltage<br>LL103A<br>LL103B<br>LL103C | V <sub>RRM</sub> | 40<br>30<br>20     | V    |
| Power Dissipation (Infinite Heatsink)              | P <sub>tot</sub> | 400 <sup>(1)</sup> | mW   |
| Single Cycle Surge 60-Hz Sine Wave                 | I <sub>FSM</sub> | 15                 | A    |
| Thermal Resistance Junciton to Ambient             | R <sub>θJA</sub> | 300 <sup>(1)</sup> | °CW  |
| Junction Temperature                               | T <sub>j</sub>   | 125                | °C   |
| Storage Temperature Range                          | T <sub>s</sub>   | -55 to +150        | °C   |

### Electrical Characteristics

(T<sub>j</sub> = 25°C unless otherwise noted)

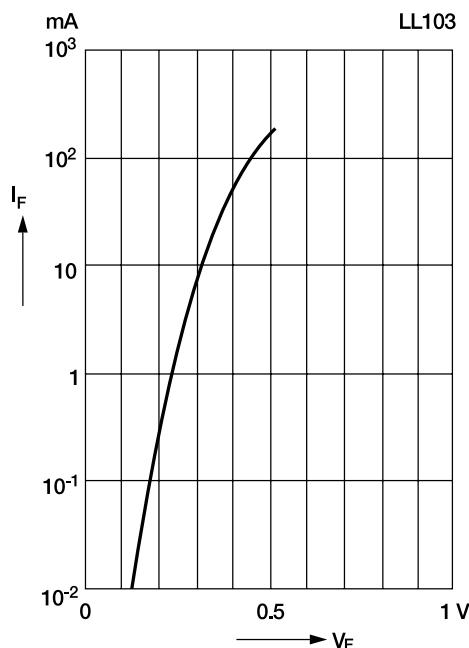
| Parameter                                     | Symbol           | Test Condition   | Min         | Typ         | Max         | Unit |
|---|------------------|--|-------------|-------------|-------------|------|
| Leakage Current<br>LL103A<br>LL103B<br>LL103C | I <sub>R</sub>   | V <sub>R</sub> = 30V<br>V <sub>R</sub> = 20V<br>V <sub>R</sub> = 10V             | —<br>—<br>— | —<br>—<br>— | 5<br>5<br>5 | μA   |
| Forward Voltage Drop                          | V <sub>F</sub>   | I <sub>F</sub> = 20mA<br>I <sub>F</sub> = 200mA                                  | —<br>—      | —<br>—      | 0.37<br>0.6 | V    |
| Junction Capacitance                          | C <sub>tot</sub> | V <sub>R</sub> = 0V, f = 1MHz  | —           | 50          | —           | pF   |
| Reverse Recovery Time                         | t <sub>rr</sub>  | I <sub>F</sub> = I <sub>R</sub> = 50mA to 200mA,<br>recover to 0.1I <sub>R</sub> | —           | —           | 10          | ns   |

**Note:** (1) Valid provided that electrodes are kept at ambient temperature.

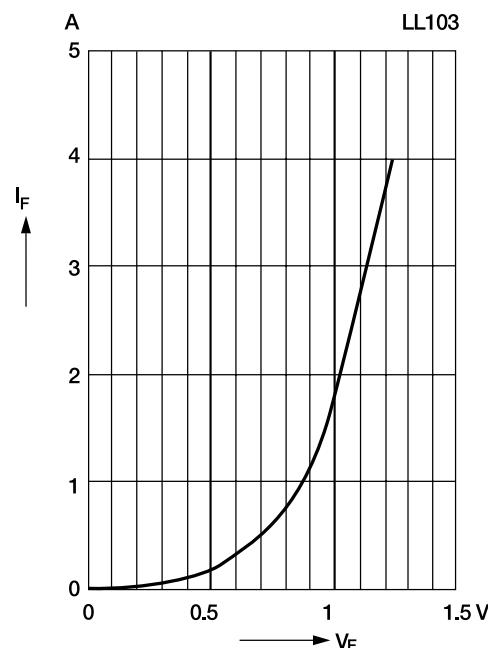


**Ratings and Characteristic Curves** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Typical variation of fwd. current vs. fwd. voltage for primary conduction through the Schottky barrier

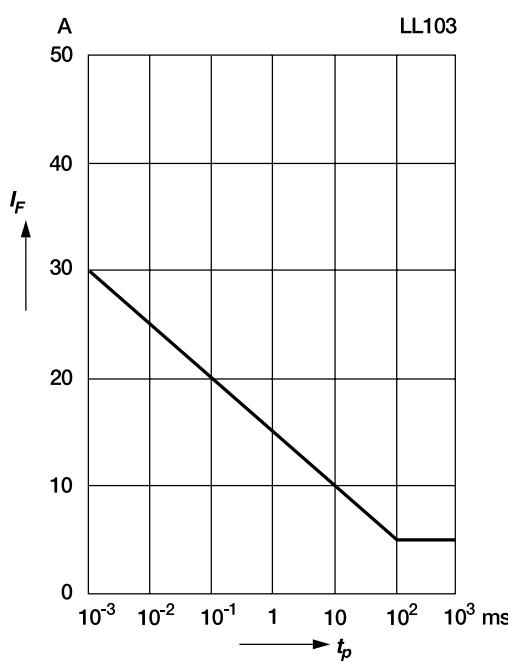


Typical high current forward conduction curve  
 $t_p = 300 \text{ ms}$ , duty cycle = 2%

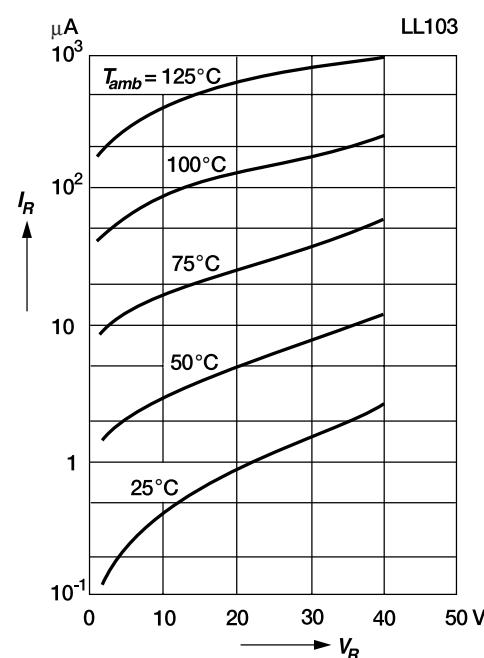


Typical non repetitive forward surge current versus pulse width

Rectangular pulse



Typical variation of reverse current at various temperatures

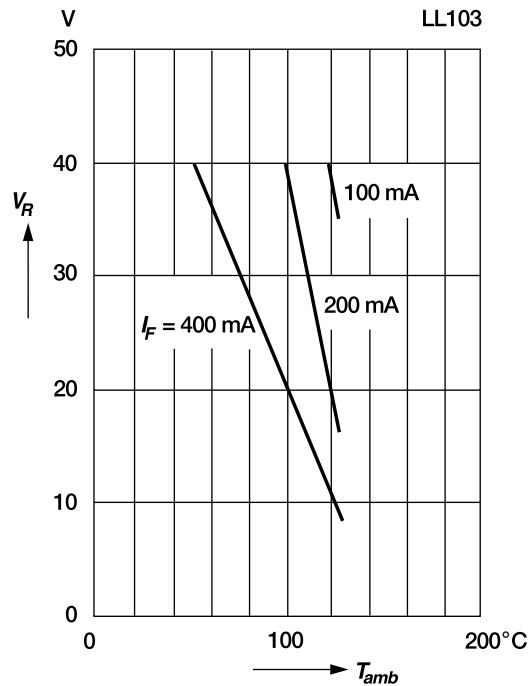


# LL103A thru LL103C



## Ratings and Characteristic Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Blocking voltage deration versus temperature at various average forward currents



Typical capacitance versus reverse voltage

